National Semiconductor

November 1994

54F/74F139
Dual 1-of-4 Decoder/Demultiplexer

General Description

The 'F139 is a high-speed, dual 1-of-4 decoder/demultiplexer. The device has two independent decoders, each accepting two inputs and providing four mutually exclusive active LOW outputs. Each decoder has an active LOW Enable input which can be used as a data input for a 4-output demultiplexer. Each half of the 'F139 can be used as a function generator providing all four minterms of two variables.

Features

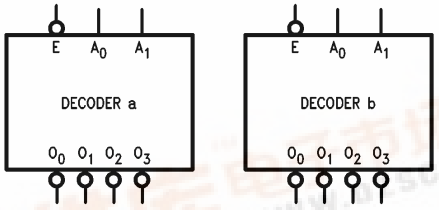
- Multifunction capability
- Two completely independent 1-of-4 decoders
- Active LOW mutually exclusive outputs
- Guaranteed 4000V minimum ESD protection

Commercial	Military	Package Number	Package Description
74F139PC		N16E	16-Lead (0.300″ Wide) Molded Dual-In-Line
	54F139DM (Note 2)	J16A	16-Lead Ceramic Dual-In-Line
74F139SC (Note 1)		M16A	16-Lead (0.150″ Wide) Molded Small Outline, JEDEC
74F139SJ (Note 1)		M16D	16-Lead (0.300″ Wide) Molded Small Outline, EIAJ
	54F139FM (Note 2)	W16A	16-Lead Cerpack
	54F139LM (Note 2)	E20A	20-Lead Ceramic Leadless Chip Carrier, Type C

Note 1: Devices also available in 13″ reel. Use suffix = SCX and SJX.

Note 2: Military grade device with environmental and burn-in processing. Use suffix = DMQB, FMQB and LMQB.

Logic Symbols



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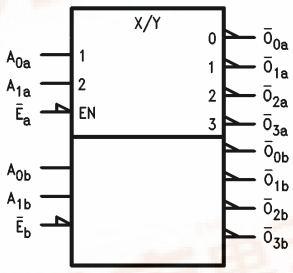
IEEE/IEC



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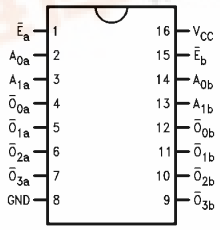
Connection Diagrams

Pin Assignment DIP, SOIC and Flatpak



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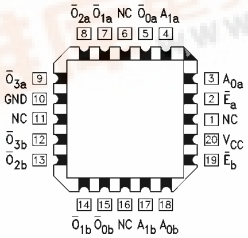
Pin Assignment for LCC



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Unit Loading/Fan Out

Pin Names	Description	54F/74F	
		U.L. HIGH/LOW	Input I_{IH}/I_{IL} Output I_{OH}/I_{OL}
A_0, A_1	Address Inputs	1.0/1.0	20 μA/ −0.6 mA
$\overline{E}$	Enable Inputs (Active LOW)	1.0/1.0	20 μA/ −0.6 mA
$\overline{O}_0$–$\overline{O}_3$	Outputs (Active LOW)	50/33.3	−1 mA/20 mA

Functional Description

The 'F139 is a high-speed dual 1-of-4 decoder/demultiplexer. The device has two independent decoders, each of which accepts two binary weighted inputs (A_0–A_1) and provides four mutually exclusive active LOW Outputs ($\overline{O}_0$–$\overline{O}_3$). Each decoder has an active LOW enable ($\overline{E}$). When $\overline{E}$ is HIGH all outputs are forced HIGH. The enable can be used as the data input for a 4-output demultiplexer application. Each half of the 'F139 generates all four minterms of two variables. These four minterms are useful in some applications, replacing multiple gate functions as shown in *Figure 1*, and thereby reducing the number of packages required in a logic network.

Truth Table

Inputs			Outputs			
$\overline{E}$	A_0	A_1	$\overline{O}_0$	$\overline{O}_1$	$\overline{O}_2$	$\overline{O}_3$
H	X	X	H	H	H	H
L	L	L	L	H	H	H
L	H	L	H	L	H	H
L	L	H	H	H	L	H
L	H	H	H	H	H	L

H = HIGH Voltage Level

L = LOW Voltage Level

X = Immaterial

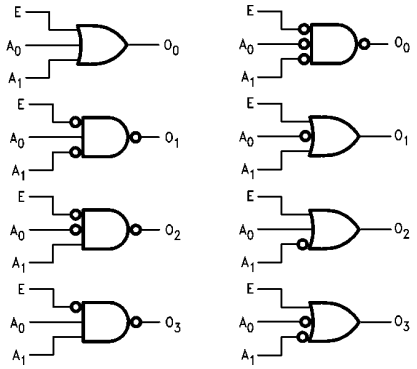

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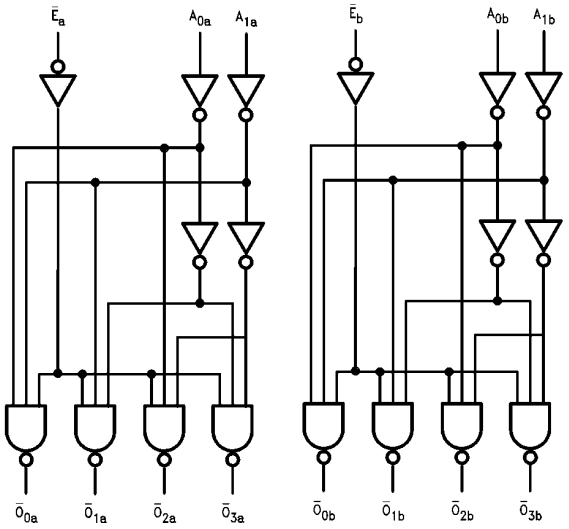
FIGURE 1. Gate Functions (each half)

Logic Diagram



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Please note that this diagram is provided only for the understanding of logic operations and should not be used to estimate propagation delays.

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Storage Temperature	−65°C to +150°C
Ambient Temperature under Bias	−55°C to +125°C
Junction Temperature under Bias	−55°C to +175°C
Plastic	−55°C to +150°C
V_{CC} Pin Potential to Ground Pin	−0.5V to +7.0V
Input Voltage (Note 2)	−0.5V to +7.0V
Input Current (Note 2)	−30 mA to +5.0 mA
Voltage Applied to Output in HIGH State (with V_{CC} = 0V)	
Standard Output	−0.5V to V_{CC}
TRI-STATE® Output	−0.5V to +5.5V
Current Applied to Output in LOW State (Max)	twice the rated I_{OL} (mA)
ESD Last Passing Voltage (Min)	4000V

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

Recommended Operating Conditions

Free Air Ambient Temperature	
Military	−55°C to +125°C
Commercial	0°C to +70°C
Supply Voltage	
Military	+4.5V to +5.5V
Commercial	+4.5V to +5.5V

DC Electrical Characteristics

Symbol	Parameter		54F/74F Min	54F/74F Typ	54F/74F Max	Units	V_{CC}	Conditions
V_{IH}	Input HIGH Voltage		2.0			V		Recognized as a HIGH Signal
V_{IL}	Input LOW Voltage				0.8	V		Recognized as a LOW Signal
V_{CD}	Input Clamp Diode Voltage				−1.2	V	Min	I_{IN} = −18 mA
V_{OH}	Output HIGH Voltage	54F 10% V_{CC}	2.5			V	Min	I_{OH} = −1 mA
		74F 10% V_{CC}	2.5					I_{OH} = −1 mA
		74F 5% V_{CC}	2.7					I_{OH} = −1 mA
V_{OL}	Output LOW Voltage	54F 10% V_{CC}			0.5	V	Min	I_{OL} = 20 mA
		74F 10% V_{CC}			0.5			I_{OL} = 20 mA
I_{IH}	Input HIGH Current	54F			20.0	μA	Max	V_{IN} = 2.7V
		74F			5.0			
I_{BVI}	Input HIGH Current Breakdown Test	54F			100	μA	Max	V_{IN} = 7.0V
		74F			7.0			
I_{CEX}	Output HIGH Leakage Current	54F			250	μA	Max	V_{OUT} = V_{CC}
		74F			50			
V_{ID}	Input Leakage Test	74F	4.75			V	0.0	I_{ID} = 1.9 μA All Other Pins Grounded
I_{OD}	Output Leakage Circuit Current	74F			3.75	μA	0.0	V_{IOD} = 150 mV All Other Pins Grounded
I_{IL}	Input LOW Current				−0.6	mA	Max	V_{IN} = 0.5V
I_{OS}	Output Short-Circuit Current		−60		−150	mA	Max	V_{OUT} = 0V
I_{CC}	Power Supply Current			13	20	mA	Max	

AC Electrical Characteristics

Symbol	Parameter	74F $T_A = +25°C$, $V_{CC} = +5.0V$, $C_L = 50$ pF			54F T_A, V_{CC} = Mil, $C_L = 50$ pF		74F T_A, V_{CC} = Com, $C_L = 50$ pF		Units
		Min	Typ	Max	Min	Max	Min	Max	
t_{PLH}	Propagation Delay	3.5	5.3	7.5	2.5	12.0	3.0	8.5	ns
t_{PHL}	A_0 or A_1 to $\overline{O}_n$	4.0	6.1	8.0	3.5	9.5	4.0	9.0	
t_{PLH}	Propagation Delay	3.5	5.4	7.0	3.0	9.0	3.5	8.0	ns
t_{PHL}	$\overline{E}_1$ to $\overline{O}_n$	3.0	4.7	6.5	2.5	8.0	3.0	7.5	

Ordering Information

74F 139 S C X

Temperature Range Family
- 74F = Commercial
- 54F = Military

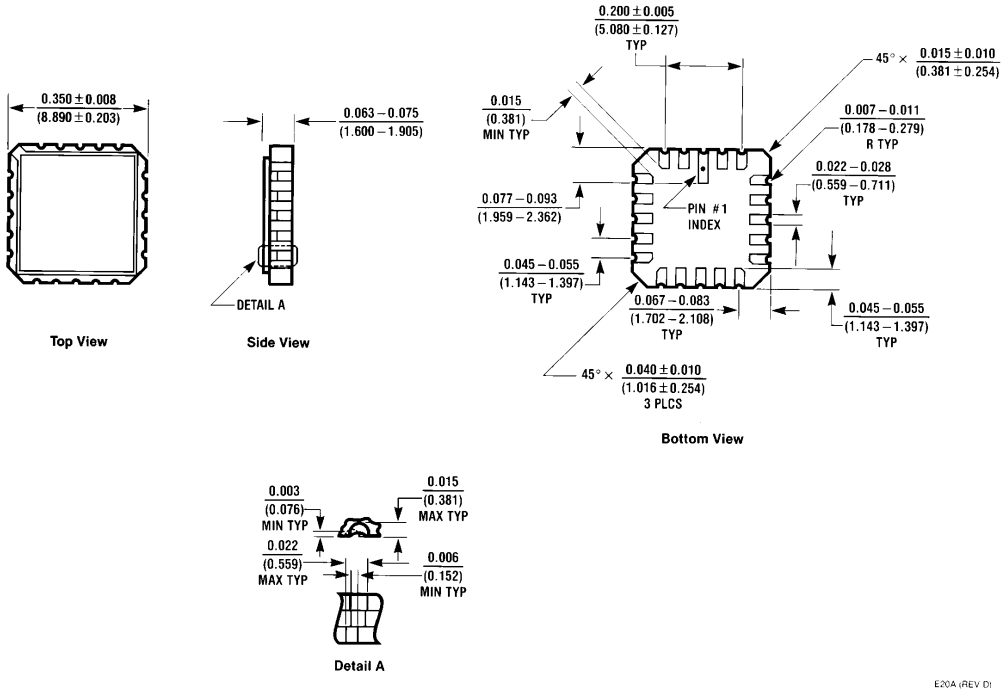
Device Type

Package Code
- P = Plastic DIP
- D = Ceramic DIP
- F = Flatpak
- L = Leadless Chip Carrier (LCC)
- S = Small Outline SOIC JEDEC
- SJ = Small Outline SOIC EIAJ

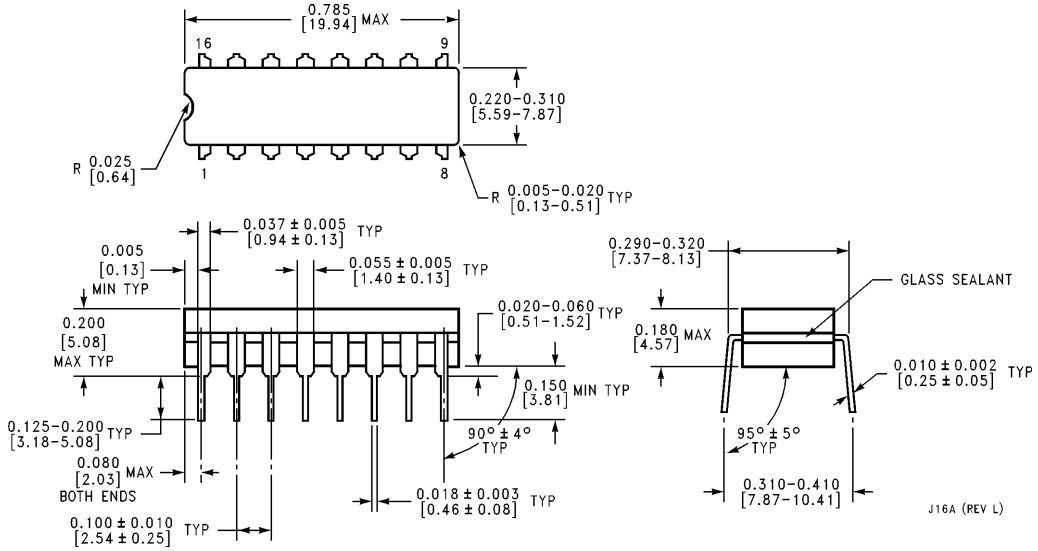
Temperature Range
- C = Commercial (0°C to +70°C)
- M = Military (−55°C to +125°C)

Special Variations
- QB = Military grade device with environmental and burn-in processing
- X = Devices shipped in 13″ reel

Physical Dimensions inches (millimeters)

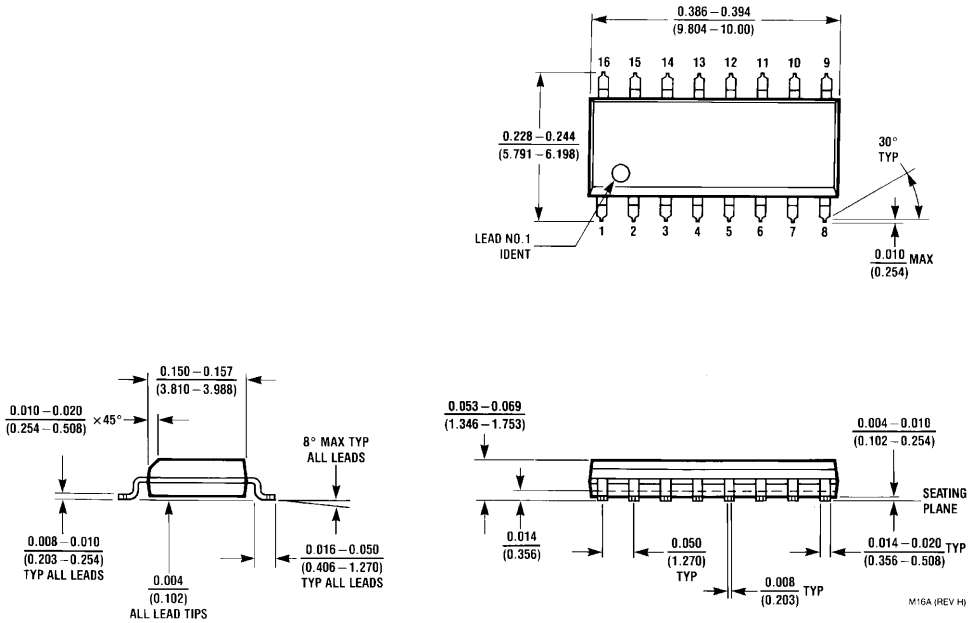


20-Lead Ceramic Leadless Chip Carrier (L)
NS Package Number E20A



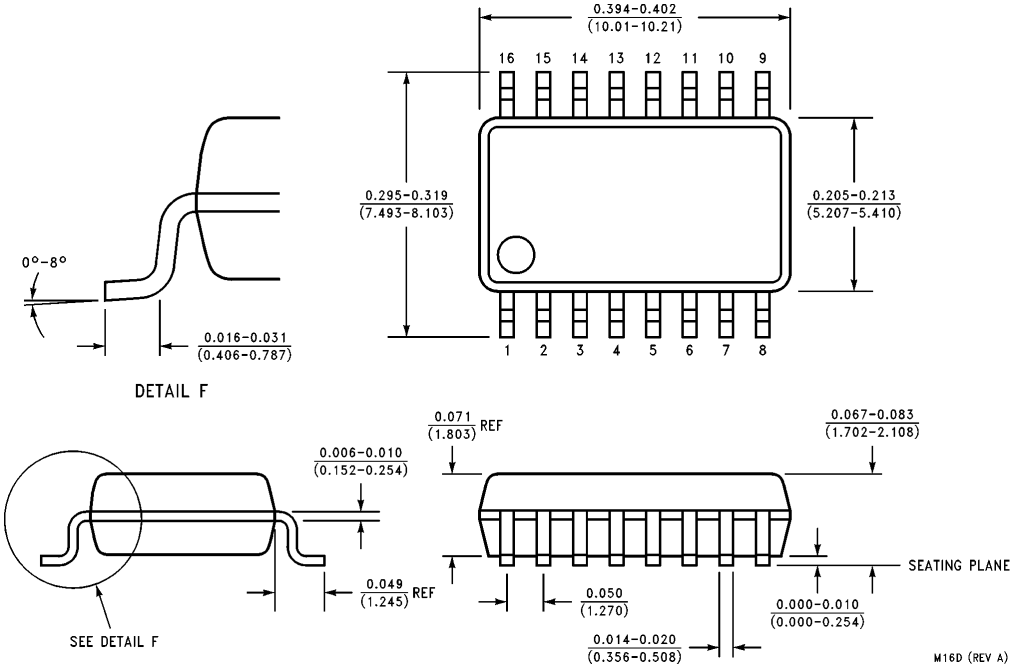
16-Lead Ceramic Dual In-Line Package (D)
NS Package Number J16A

Physical Dimensions inches (millimeters) (Continued)

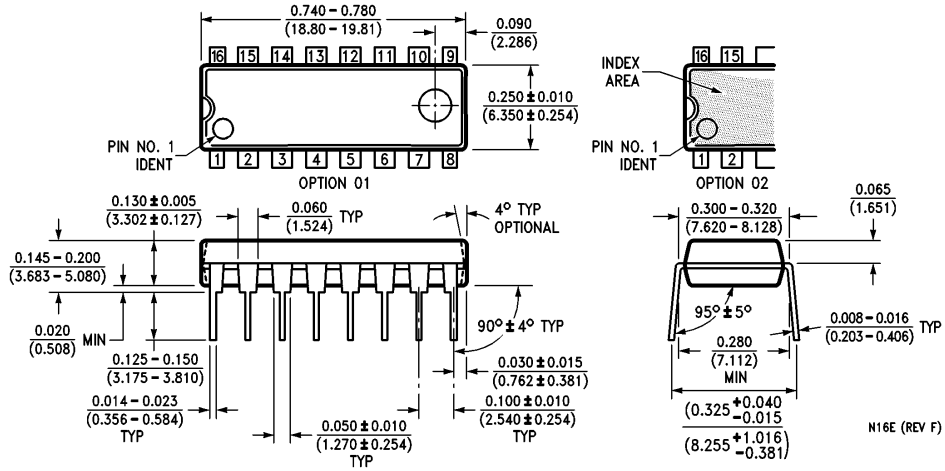


16-Lead (0.150″ Wide) Molded Small Outline Integrated Circuit (S)
NS Package Number M16A

Physical Dimensions inches (millimeters) (Continued)

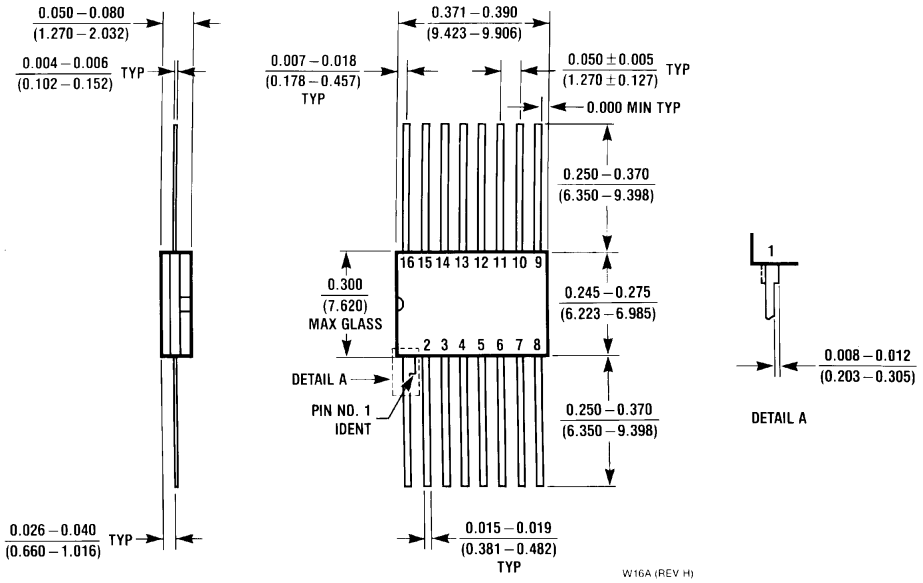


16-Lead (0.300″ Wide) Molded Small Outline Package, EIAJ (SJ)
NS Package Number M16D



16-Lead (0.300″ Wide) Molded Dual In-Line Package (P)
NS Package Number N16E

Physical Dimensions inches (millimeters) (Continued)



16-Lead Ceramic Flatpak (F)
NS Package Number W16A

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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